



Reliability Report: DS1808

Process: 1P, 1M, 5.0um, 30V NF & PF, UVNd, UVPd, N+ESD, TEOS Spacer, Passivation w/Nov TEOS Oxide-Nitride

Metal: Al / 0.5% Cu / 0.8% Si Gate Ox Thickness: 225 Å Pin Count: 16
 Cf: 60% Tuse: 25 °C Assembly: ATP (Amkor, PI)
 Ea: 0.7 Vuse: 5.5 Volts Package: SOIC
 β: 0 Body Size: 150x1.4

Summary Data with Chi-Square Distribution Assumed.
 Stress Ambient Temperature and Voltage to
 Field Ambient Temperature And Voltage

DESCRIPTION	VEHICLE	REV	DATE CODE	CONDITION	READPOINT	QUANTITY	FAILS	FILE #	DEVICE HRS
HIGH TEMPERATURE OPERATING LIFE									
HIGH VOLTAGE LIFE	DS1808	A2	0133	125C, 6.0 V (PSA) & +13.2 V (PS	6	HOURS	80	0	452720
	DS1808	A2	0133	125C, 6.0 V (PSA) & +13.2 V (PS	336	HOURS	80	0	24899612
				DEVICE HRS:	2.54E+07	TOTALS:	0		
				FAILURE RATE	MTBF (yrs): 3158	FITS:	36		

PRODUCT	REV	DIE SIZE (x)	DIE SIZE (y)	No. of Transistors
DS1808	A2	159	80	1700

Thursday, May 16, 2002